

Digital transistor (Common Emitter Dual Transistors)

UMA9N / FMA9N

●Features

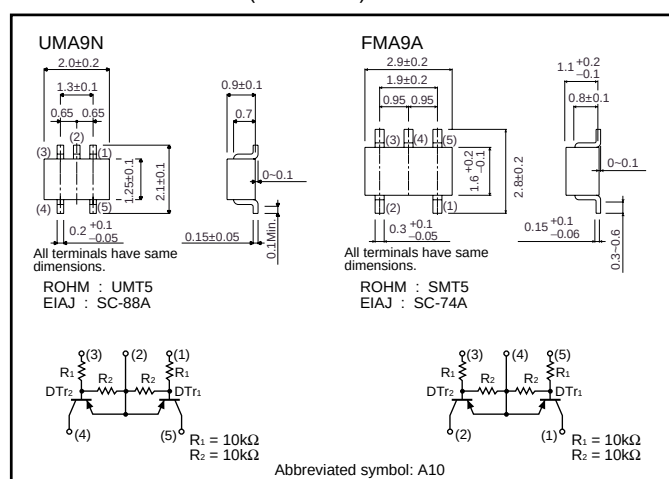
- 1) Two DTA114E chips in UMT and SMT packages.
- 2) Mounting cost and area can be cut in half.

●Structure

Epitaxial planar type
PNP silicon transistor
(Built-in resistor type)

The following characteristics apply to both DTr1 and DTr2.

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Supply voltage	V _{CC}	-50	V
Input voltage	V _{IN}	-40 10	V
Output current	I _O	-50	mA
	I _{C (MAX.)}	-100	
Power dissipation	UMA9N FMA9A	150 (TOTAL) 300 (TOTAL)	mW
			*1 *2
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-50~+150	°C

*1 120mW per element must not be exceeded.

*2 200mW per element must not be exceeded.

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	V _{I (off)}	-	-	-0.5	V	V _{CC} = -5V, I _O = -100μA
	V _{I (on)}	-3.0	-	-		V _O = -0.3V, I _O = -10mA
Output voltage	V _{O (on)}	-	-0.1	-0.3	V	I _O /I _I = -10mA / -0.5mA
Input current	I _I	-	-	-0.88	mA	V _I = -5V
Output current	I _{O (off)}	-	-	-0.5	μA	V _{CC} = -50V, V _I = 0V
DC current gain	G _I	30	-	-	-	I _O = -5mA, V _O = -5V
Transition frequency	f _T	-	250	-	MHz	V _{CE} = -10mA, I _E = 5mA, f = 100MHz *
Input resistance	R _I	7	10	13	kΩ	-
Resistance ratio	R ₂ /R ₁	0.8	1	1.2	-	-

* Transition frequency of the device

Transistors

●Packaging specifications

Part No.	Packaging type	Taping	
	Code	TR	T148
	Basic ordering unit (pieces)	3000	3000
UMA9N		○	-
FMA9A		-	○

●Electrical characteristic curves

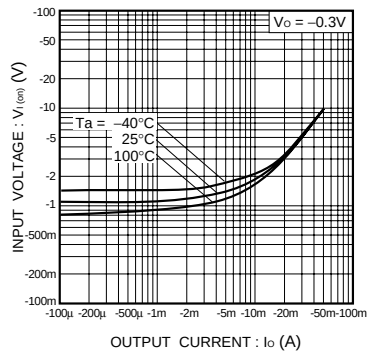


Fig.1 Input voltage vs. output current
(ON characteristics)

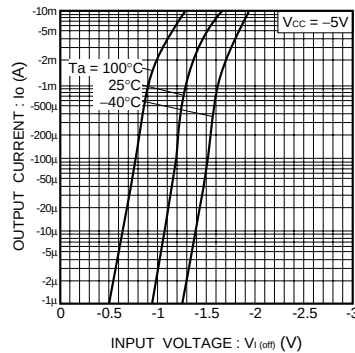


Fig.2 Output current vs. input voltage
(OFF characteristics)

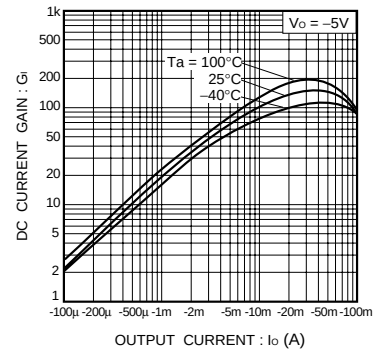


Fig.3 DC current gain vs. output
current

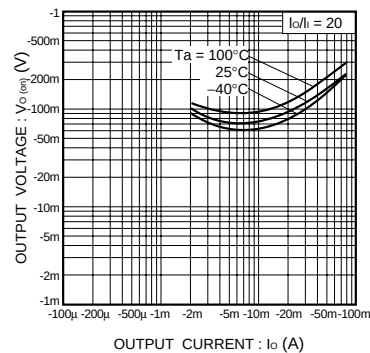


Fig.4 Output voltage vs. output
current